

# Anton Kozhukhov

## List of Publications by Year in descending order

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64  
papers

658  
citations

840776

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h-index

580821

25  
g-index

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all docs

64  
docs citations

64  
times ranked

879  
citing authors

#	ARTICLE	IF	CITATIONS
1	Interaction of low-fluence femtosecond laser pulses with a composite layer containing Ge nanoclusters: A novel type of nanofoam formation. Journal of Laser Applications, 2022, 34, 022002.	1.7	1
2	Electrophysical parameter comparison of 2DEG in AlGaIn/GaN heterostructures grown by the NH <sub>3</sub> -MBE technique on sapphire and silicon substrates. Journal of Crystal Growth, 2022, 588, 126669.	1.5	3
3	InAs Islands Formation on the InP(001) During High- Temperature Annealing in an As Flux. , 2021, , .		0
4	Preparation of Atomically Clean and Structurally Ordered Surfaces of Epitaxial CdTe Films for Subsequent Epitaxy. Semiconductors, 2021, 55, S62-S66.	0.5	5
5	Nanowired structure, optical properties and conduction band offset of RF magnetron-deposited n-SiIn <sub>2</sub> O <sub>3</sub> :Er films.. Materials Research Express, 2020, 7, 125903.	1.6	4
6	Growth of Nitride Heteroepitaxial Transistor Structures: from Epitaxy of Buffer Layers to Surface Passivation. Optoelectronics, Instrumentation and Data Processing, 2020, 56, 485-491.	0.6	4
7	From Self-Organization of Monoatomic Steps on the Silicon Surface to Subnanometer Metrology. Optoelectronics, Instrumentation and Data Processing, 2020, 56, 533-544.	0.6	3
8	About the nature of the barrier inhomogeneities at Au/Ti/n-InAlAs(001) Schottky contacts. Applied Physics Letters, 2019, 114, .	3.3	6
9	Undoped High-Resistance GaN Buffer Layer for AlGaIn/GaN High-Electron-Mobility Transistors. Technical Physics Letters, 2019, 45, 761-764.	0.7	5
10	Microstructure and dispersive optical parameters of iron films deposited by the thermal evaporation method. Optik, 2019, 188, 120-125.	2.9	2
11	Forming the GaN Nanocrystals on the Graphene-Like g-AlN and g-Si <sub>3</sub> N <sub>3</sub> Surface. Physics of the Solid State, 2019, 61, 2329-2334.	0.6	1
12	MORPHOLOGICAL AND CHEMICAL CHARACTERIZATION OF MAGNESIUM PHOSPHATE AND CALCIUM PHOSPHATE BIONS. Siberian Medical Review, 2019, 3, 34-42.	0.2	0
13	Local Anodic Oxidation of Thin GeO Films and Formation of Nanostructures Based on Them. Physics of the Solid State, 2018, 60, 700-704.	0.6	2
14	Thermal Smoothing and Roughening of GaAs Surfaces: Experiment and Monte Carlo Simulation. Semiconductors, 2018, 52, 618-621.	0.5	6
15	Photoemission properties of flat and rough GaAs surfaces with cesium and oxygen layers. Journal of Physics: Conference Series, 2018, 993, 012007.	0.4	1
16	Step Patterns on {100} Faces of Diamond Crystals As-Grown in Mg-Based Systems. Crystal Growth and Design, 2018, 18, 152-158.	3.0	8
17	Atomic Force Microscopy Local Oxidation of GeO Thin Films. Semiconductors, 2018, 52, 2081-2084.	0.5	0
18	Elastic Properties of Suspended Conducting GaAs/AlGaAs Nanostructures by Means of Atomic Force Microscopy. Optoelectronics, Instrumentation and Data Processing, 2018, 54, 496-501.	0.6	0

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19	Formation of a Graphene-Like SiN Layer on the Surface Si(111). Semiconductors, 2018, 52, 1511-1517.	0.5	4
20	Spectroscopy of Single AlInAs Quantum Dots. Optoelectronics, Instrumentation and Data Processing, 2018, 54, 168-174.	0.6	0
21	The initial stages of atomic force microscope based local anodic oxidation of silicon. AIP Advances, 2018, 8, .	1.3	6
22	Influence of a silicon impurity on growth of diamond crystals in the Mg-C system. Diamond and Related Materials, 2018, 87, 27-34.	3.9	2
23	Dislocation etching of diamond crystals grown in Mg-C system with the addition of silicon. Diamond and Related Materials, 2018, 88, 67-73.	3.9	8
24	Local monitoring of atomic steps on GaAs(001) surface under oxidation, wet removal of oxides and thermal smoothing. Applied Surface Science, 2017, 406, 307-311.	6.1	7
25	Formation of GaAs Step-Terraced Surfaces by Annealing in Equilibrium Conditions. , 2017, , 255-277.		0
26	Superminiature Radiation Sources Based on Semiconductor Nanostructures. , 2017, , 437-461.		1
27	Reversible electrochemical modification of the surface of a semiconductor by an atomic-force microscope probe. Semiconductors, 2017, 51, 420-422.	0.5	2
28	Thermodynamic and kinetic roughening: Monte Carlo simulation and experiment on GaAs. Journal of Physics: Conference Series, 2017, 816, 012008.	0.4	2
29	AlInAs quantum dots. JETP Letters, 2017, 105, 103-109.	1.4	4
30	Conductive indium nanowires deposited on silicon surface by dip-pen nanolithography. Journal of Physics: Conference Series, 2017, 917, 032005.	0.4	0
31	Formation and crystal structure of GaSb/GaP quantum dots. Bulletin of the Russian Academy of Sciences: Physics, 2016, 80, 17-22.	0.6	4
32	Indium nanowires at the silicon surface. Semiconductors, 2016, 50, 901-903.	0.5	0
33	Crystal growth of Bi <sub>2</sub> Te <sub>3</sub> and noble cleaved (0001) surface properties. Journal of Solid State Chemistry, 2016, 236, 203-208.	2.9	31
34	InAs-based metal-oxide-semiconductor structure formation in low-energy Townsend discharge. Applied Physics Letters, 2015, 107, .	3.3	16
35	Increase in the diffusion length of minority carriers in Al <sub>x</sub> Ga <sub>1-x</sub> N alloys ( x = 0-0.1) fabricated by ammonia molecular beam epitaxy. Semiconductors, 2015, 49, 1285-1289.	0.5	6
36	Structure and optical properties of Si and SiGe layers grown on SiO <sub>2</sub> by chemical vapor deposition. Thin Solid Films, 2015, 579, 131-135.	1.8	14

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37	Optical and electrical properties of silicon nanopillars. Semiconductors, 2015, 49, 939-943.	0.5	5
38	Efficient single-photon emitters based on Bragg microcavities containing selectively positioned InAs quantum dots. Semiconductors, 2015, 49, 33-38.	0.5	4
39	Highly conductive indium nanowires deposited on silicon by dip-pen nanolithography. Journal of Applied Physics, 2015, 117, .	2.5	1
40	Growth of CdWO <sub>4</sub> crystals by the low thermal gradient Czochralski technique and the properties of a (010) cleaved surface. Journal of Crystal Growth, 2014, 401, 156-159.	1.5	17
41	Growth, optical and microstructural properties of PbB <sub>4</sub> O <sub>7</sub> plate crystals. Optical Materials, 2014, 37, 298-301.	3.6	11
42	Defects in GaSe grown by Bridgman method. Journal of Microscopy, 2014, 256, 208-212.	1.8	21
43	Study of the morphology and optical properties of anodic oxide layers on InAs (111)III. Semiconductors, 2013, 47, 555-560.	0.5	1
44	High-precision nanoscale length measurement. Nanotechnologies in Russia, 2013, 8, 518-531.	0.7	7
45	Growth of AlGa <sub>N</sub> /Ga <sub>N</sub> heterostructures with a two-dimensional electron gas on AlN/Al <sub>2</sub> O <sub>3</sub> substrates. Optoelectronics, Instrumentation and Data Processing, 2013, 49, 429-433.	0.6	9
46	Surface morphology of Si layers grown on SiO <sub>2</sub> . Applied Surface Science, 2013, 267, 40-44.	6.1	4
47	Structure, microrelief and optical properties of chromium films deposited by sublimation in vacuum. Letters on Materials, 2013, 3, 326-329.	0.7	3
48	AFM tip-induced modification of semiconductor surface properties. , 2012, , .		0
49	Nanointervention into crystal flatland. III. Crystal growth and micromorphology of cleaved GaSe(001) surface. , 2012, , .		0
50	Inertness and degradation of (0001) surface of Bi <sub>2</sub> Se <sub>3</sub> topological insulator. Journal of Applied Physics, 2012, 112, .	2.5	57
51	The role of Euler buckling instability in the fabrication of nanoelectromechanical systems on the basis of GaAs/AlGaAs heterostructures. Applied Physics Letters, 2012, 101, .	3.3	10
52	Formation of DNA molecules ordered systems on silicon surfaces. , 2012, , .		0
53	Characterization of GaAs(001) step-terraced morphology formation. , 2012, , .		1
54	Folding of acoustic-phonon modes in GaAs/AlAs (311)A superlattices in the direction perpendicular to nanofacets. JETP Letters, 2012, 95, 70-73.	1.4	4

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55	AFM study of atomic-flat terraces on ZnWO <sub>4</sub> (010) cleaved surface. , 2011, , .		1
56	Formation of Arrays of Free-Standing CdS Quantum Dots Using the Langmuir-Blodgett Technique. Journal of Physical Chemistry C, 2011, 115, 20148-20152.	3.1	19
57	Stability of (0001) Bi <sub>2</sub> Te <sub>3</sub> surface. , 2011, , .		0
58	Formation of Inert Bi <sub>2</sub> Se <sub>3</sub> (0001) Cleaved Surface. Crystal Growth and Design, 2011, 11, 5507-5514.	3.0	112
59	Nucleation Of Ge 3D-islands On Pit-patterned Si Substrates. , 2011, , .		0
60	Stability of the (0001) surface of the Bi <sub>2</sub> Se <sub>3</sub> topological insulator. JETP Letters, 2011, 94, 465-468.	1.4	20
61	Structural and Electronic Properties of ZnWO <sub>4</sub> (010) Cleaved Surface. Crystal Growth and Design, 2011, 11, 2479-2484.	3.0	153
62	Epitaxial growth of ZnO nanocrystals at ZnWO <sub>4</sub> (010) cleaved surface. Journal of Crystal Growth, 2011, 318, 1147-1150.	1.5	34
63	Space arrangement of Ge nanoislands formed by growth of Ge on pit-patterned Si substrates. Journal of Crystal Growth, 2011, 323, 198-200.	1.5	6
64	Clustering of CdS nanocrystals during evaporation of Langmuir &#x2014; Blodgett matrix. , 2010, , .		0